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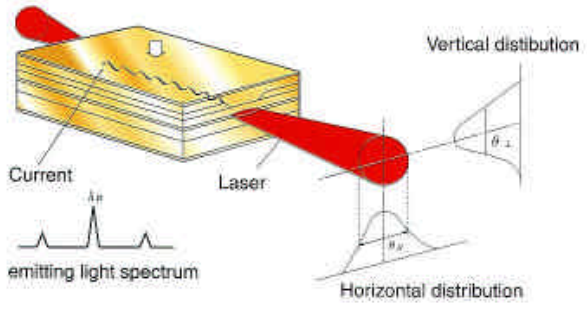
CHIP 1310L TECHNICAL DATA

Infrared Wavelength Laserdiodechip

Structure: **index guided, single transverse mode**
Lasing wavelength: **1310 nm typ.**
Max. optical power: **5 mW typ.**
Chipsize: **300 x 300 x 100 µm** [L x W x H] **+/- 20 µm**
Cavity length: **300 µm +/- 5 µm**
Emitting Point Height: **1.6 - 1.8 µm from P-side**
Coating: Au coated on upper and lower side n-side: 4000Å, p-side: 4000Å
Low threshold current, low operating current, low noise



Absolute Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	5	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
Operation Temperature	T_C	-10 .. +50	°C
Storage Temperature	T_{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	kink free		5		mW
Emitting Aperture	A	P_o = 5 mW		1 x 2		µm²
Threshold Current	I_{th}			10	12	mA
Operation Current	I_{op}	P_o = 5 mW		25	30	mA
Operating Voltage	V_{op}	P_o = 5 mW		1.2		V
Lasing Wavelength	λ_p	P_o = 5 mW	1280	1310	1340	nm
Beam Divergence	$\theta_{//}$	P_o = 5 mW		20		°
Beam Divergence	$\theta_{\perp}$	P_o = 5 mW		40		°